





DMP4051LK3

40V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = 25°C		
-40V	51mΩ @ V _{GS} = -10V	-10.5A		
	85mΩ @ V _{GS} = -4.5V	-8.4A		

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance (R_{DS(on)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions



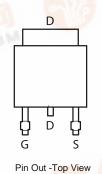
- Low on-resistance
- Fast switching speed
- Green" component and RoHS compliant (Note 1)

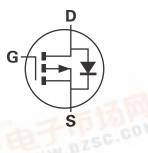
Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Below
- Ordering Information: See Below
- Weight: 0.33 grams (approximate)



Top View





Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMP4051LK3-13	P4051L	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



>:! = Manufacturer's Marking P4051L = Product Type Marking Code YYWW = Date Code Marking YY = Year (ex: 09 = 2009) WW = Week (01-52)







Maximum Ratings @T_A = 25°C unless otherwise specified

Cha	racteristic		Symbol Value		Unit	
Drain-Source voltage			V _{DSS}	-40	V	
Gate-Source voltage			V _{GS}	±20	V	
Continuous Drain current		(Note 3)	Ι _D	-10.5		
	$V_{GS} = 10V$	T _A =70°C (Note 3)		-8.40	А	
		(Note 2)		-7.2		
Pulsed Drain current V _{GS} = 10V (Note 4)		I _{DM}	-28.9	А		
Continuous Source current (Body diode) (Note 3)		Is	-10.1	А		
Pulsed Source current (Body diode) (Note 4)		I _{SM}	-28.9	А		

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit		
	(Note 2)		4.18 33.4		
Power dissipation Linear derating factor	(Note 3)	PD	8.9 71.4	W mW/°C	
	(Note 5)	-	2.14 17.1		
Thermal Resistance, Junction to Ambient	(Note 2) (Note 3) (Note 5)	R _{0JA}	29.9 14.0 58.4	°C/W	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{ ext{ heta}JL}$	2.46		
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	٥°C	

2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is Notes: measured when operating in a steady-state condition.

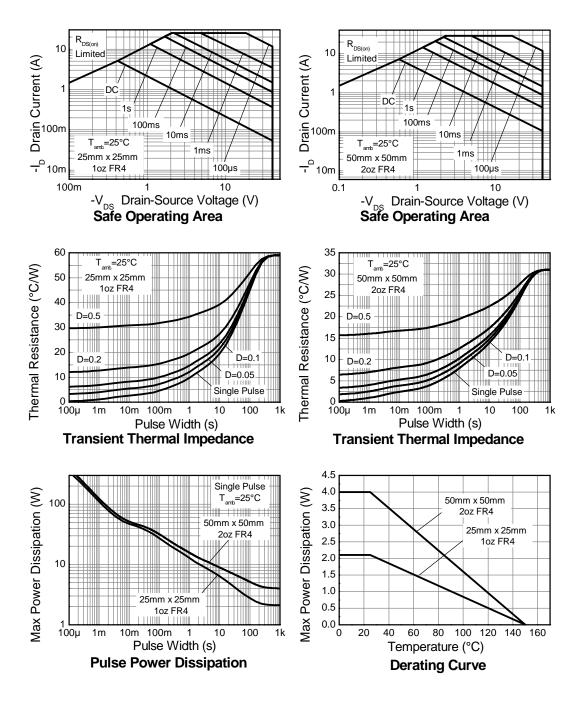
3. Same as note 2, except the device is measured at t \leq 10 sec. 4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature. 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.

6. Thermal resistance from junction to solder-point (at the end of the drain lead).





Thermal Characteristics







Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test	Condition
OFF CHARACTERISTICS						•	
Drain-Source Breakdown Voltage	BV _{DSS}	-40	_	_	V	I _D = -250μA, V _{GS} = 0V	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.5	μΑ	V _{DS} = -40V, V _G	_S = 0V
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V_{GS} = ±20V, V_{D}	_S = 0V
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(th)}	-1.0		-3.0	V	I_{D} = -250µA, V_{D}	_S = V _{GS}
Static Drain-Source On-Resistance (Note 7)	P			0.051	Ω	V_{GS} = -10V, I_{D} =	-12A
	R _{DS (ON)}			0.085	12	V _{GS} = -4.5V, I _D =	= -8A
Forward Transconductance (Notes 7 & 8)	g fs	_	16.6	_	S	V _{DS} = -15V, I _D = -12A	
Diode Forward Voltage (Note 7)	V _{SD}	_	-0.98	-1.2	V	I _S = -12A, V _{GS} = 0V	
Reverse recovery time (Note 8)	t _{rr}		138	_	ns	—I _S = -12A, di/dt= 100A/μs	
Reverse recovery charge (Note 8)	Q _{rr}	—	841	_	nC		
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	674	_	pF	− V _{DS} = -20V, V _{GS} = 0V − f= 1MHz	
Output Capacitance	C _{oss}	_	115	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	67.7	_	pF		
Total Gate Charge	Qg	_	7.0	—	nC	V _{GS} = -4.5V	
Total Gate Charge	Qg	_	14	—	nC		V _{DS} = -20V
Gate-Source Charge	Q _{gs}	_	2.2	—	nC	V _{GS} = -10V	I _D = -12A
Gate-Drain Charge	Q _{gd}	_	3.7		nC		
Turn-On Delay Time (Note 9)	t _{D(on)}	_	2.3	_	ns		
Turn-On Rise Time (Note 9)	tr	_	14.1	_	ns	V _{DD} = -20V, V _{GS} = -10V	
Turn-Off Delay Time (Note 9)	t _{D(off)}	_	25.1	_	ns	I _D = -12A, R _G ≅ 6.0Ω	
Turn-Off Fall Time (Note 9)	t _f	_	14.3	_	ns	7	

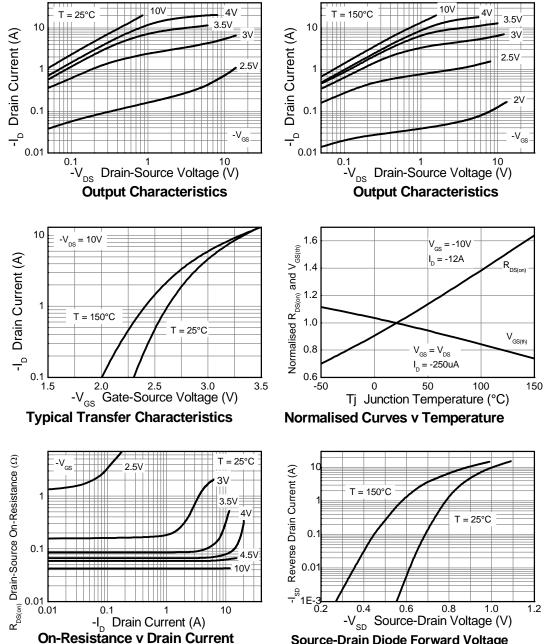
Notes:

Measured under pulsed conditions. Pulse width ≤ 300µs; duty cycle ≤ 2%
For design aid only, not subject to production testing.
Switching characteristics are independent of operating junction temperatures.





Typical Characteristics

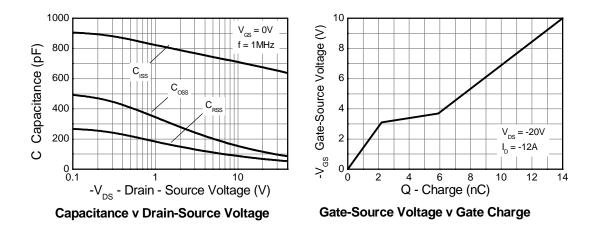


Source-Drain Diode Forward Voltage

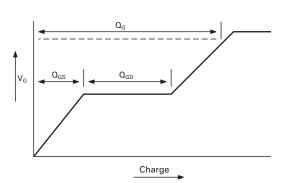




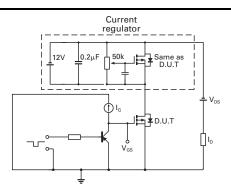
Typical Characteristics - continued



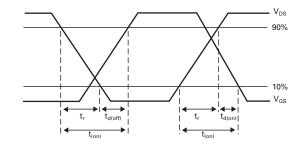
Test Circuits



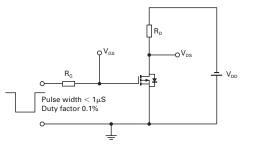




Gate charge test circuit



Switching time waveforms

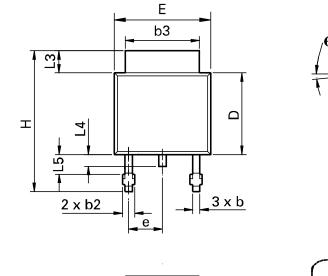


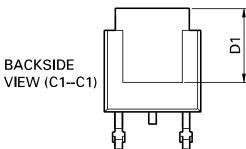
Switching time test circuit

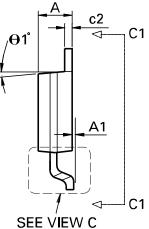


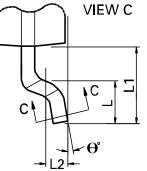


Package Outline Dimensions





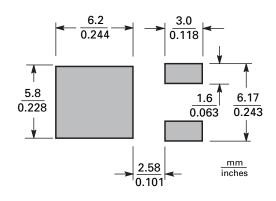




DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
А	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
с	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
Е	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	_	-	-	-



Suggested Pad Layout



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